

# Solving CMP Challenges in High Volume SiC Production

## OPTIMIZING CMP PROCESSES FOR SILICON CARBIDE WAFERS

Without the right chemical-mechanical planarization (CMP) pads and process parameters, the benefits of silicon carbide (SiC) become harder to realize.

## PLANARIZING AROUND SURFACE DEFECTIVITY

SiC wafers often arrive with surface defects, so manufacturers must select the right tools and workflows to preserve the integrity of the material while achieving the desired planarity.

## MATCHING DENSITY WITH OPTIMIZED SLURRY

SiC-optimized slurries overcome the density of the material by creating and removing an oxidized layer, but the slurry particles must remove the layer without going too deep and scratching the surface.

## Learn How Entegris Solves SiC CMP Challenges

Defectivity and hardness are just two of the main obstacles to consistent, high-volume SiC planarization. As an expert on SiC planarization, Entegris can help you solve challenges related to:

- Low material removal rate
- Increased pad temperatures
- Higher cost of ownership

With Entegris, manufacturers have the opportunity to increase wafer throughput without sacrificing quality or increasing costs.

Learn more about all the key process challenges SiC poses for CMP and how these challenges are being addressed – including several real-world examples.



Download our paper:  
*Solving CMP Challenges in  
High-Volume SiC Production*

### LEARN MORE

No other company has both the expertise and experience to provide transformative new solutions for your processes. For more information, please contact [customer service](#).



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